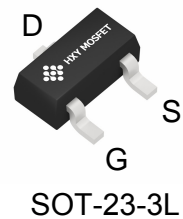




General Description

The FDN8601 use advanced SGT MOSFET technology to provide low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics.

This device is specially designed to get better ruggedness and suitable to use in



General Features

$V_{DS} = 100V$ $I_D = 5A$

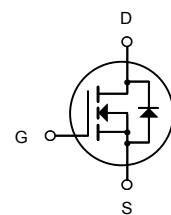
$R_{DS(ON)} < 140m\Omega @ V_{GS} = 10V$

Applications

Consumer electronic power supply Motor control

Synchronous-rectification Isolated DC

Synchronous-rectification applications



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
FDN8601	SOT-23-3L	HXY MOSFET	3000

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2.2	A
I_{DM}	Pulsed Drain Current ²	11	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JC}$	Thermal Resistance from Junction-to-Ambient ³	80	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	125	$^\circ C/W$



Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	100	110	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics <small>note3</small>						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.95	3.0	V
R _{DS(on)}	Static Drain-Source On-Resistance <small>note2</small>	V _{GS} = 10V, I _D = 3A	-	95	140	mΩ
Dynamic Characteristics <small>note4</small>						
C _{iss}	Input Capacitance	V _{DS} = 50V, V _{GS} = 0V, f = 1.0MHz	-	196	-	pF
C _{oss}	Output Capacitance		-	25.9	-	pF
C _{rss}	Reverse Transfer Capacitance		-	21.4	-	pF
Q _g	Total Gate Charge	V _{DS} = 50V, I _D = 3A, V _{GS} = 10V	-	4.3	-	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.1	-	nC
Switching Characteristics <small>note4</small>						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 50V, I _{DS} =3A R _G = 2Ω, V _{GEN} = 10V	-	14.7	-	ns
t _r	Turn-On Rise Time		-	3.5	-	ns
t _{d(off)}	Turn-Off Delay Time		-	20.9	-	ns
t _f	Turn-Off Fall Time		-	2.7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current <small>note2</small>		-	-	4.5	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	12	A
V _{SD}	Drain to Source Diode Forward Voltage <small>note3</small>	V _{GS} = 0V, I _S =3A	-	-	1.3	V
t _{rr}	Body Diode Reverse Recovery Time	V _{GS} = 0V, I _F = 3A, di/dt =100A/μs	-	32.1	-	ns
Q _{rr}	Body Diode Reverse Recovery Time Charge		-	39.4	-	nC
I _{rrm}	Peak Reverse Recovery Current		-	2.1	-	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. $V_{DD}=50$ V, $R_G=50$ Ω , $L=0.3$ mH, starting $T_J=25$ $^{\circ}\text{C}$



Typical Characteristics

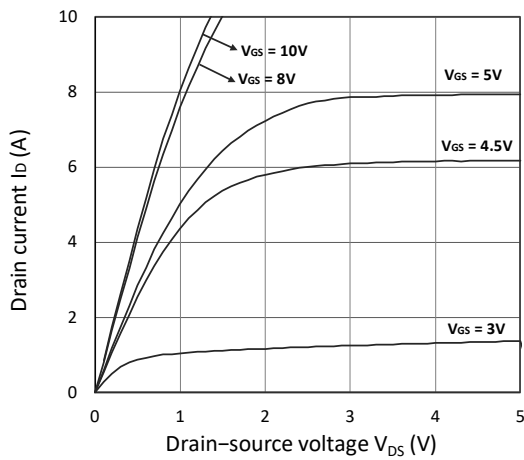


Figure 1. Output Characteristics

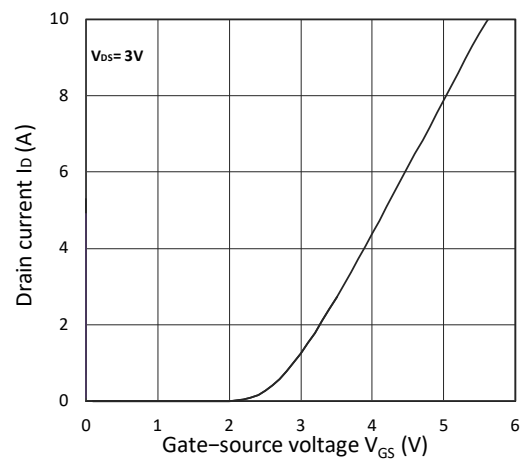


Figure 2. Transfer Characteristics

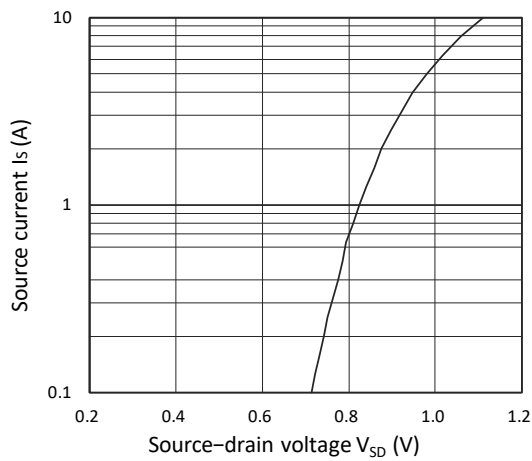


Figure 3. Forward Characteristics of Reverse

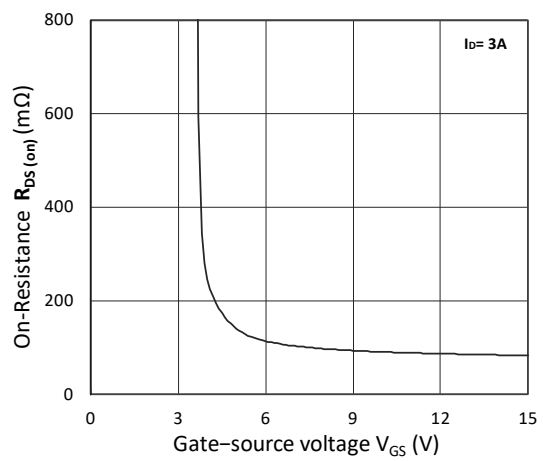


Figure 4. $R_{DS(on)}$ vs. V_{GS}

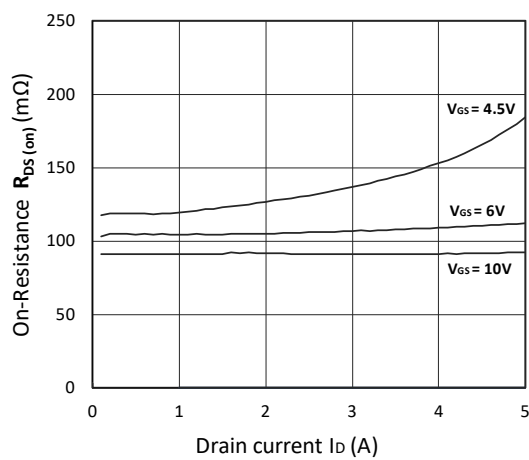


Figure 5. $R_{DS(on)}$ vs. I_D

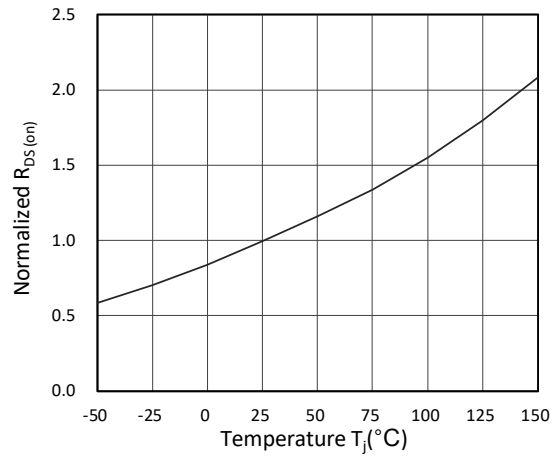


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

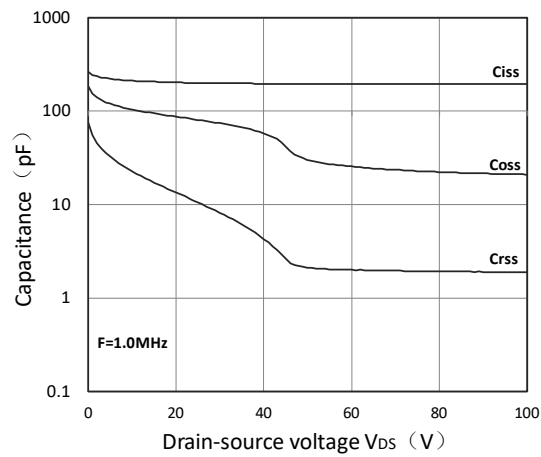


Figure 7. Capacitance Characteristics

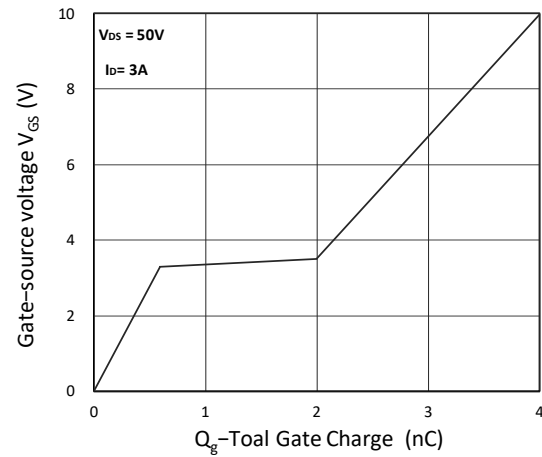
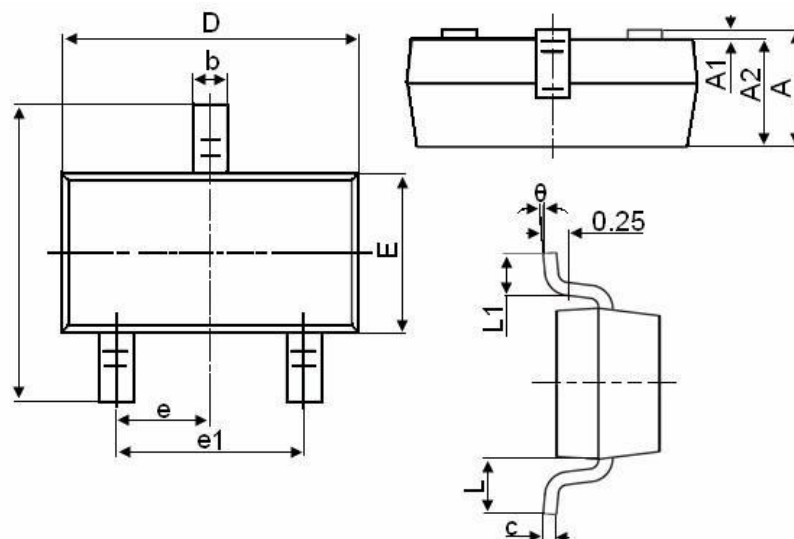


Figure 8. Gate Charge Characteristics



SOT-23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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